



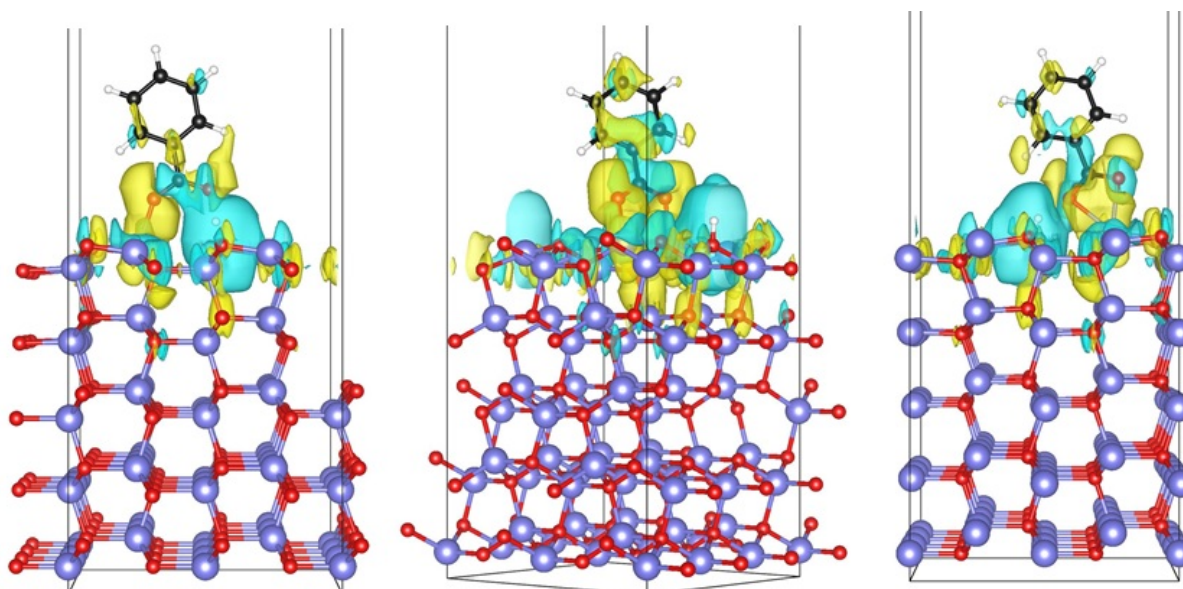
## 2. Three-dimensional mapping of electronic charge density difference ( $\Delta\rho$ ) for representative SAM/ZnO interfaces.

$$\Delta\rho = \rho_{\text{BA/ZnO}} - [\rho_{\text{BA}} + \rho_{\text{ZnO}} + \rho_{\text{H}}] \quad \text{for BA/ZnO interface.}$$

$$\Delta\rho = \rho_{\text{4TBP/ZnO}} - [\rho_{\text{4TBP}} + \rho_{\text{ZnO}}] \quad \text{for 4TBP/ZnO interface.}$$

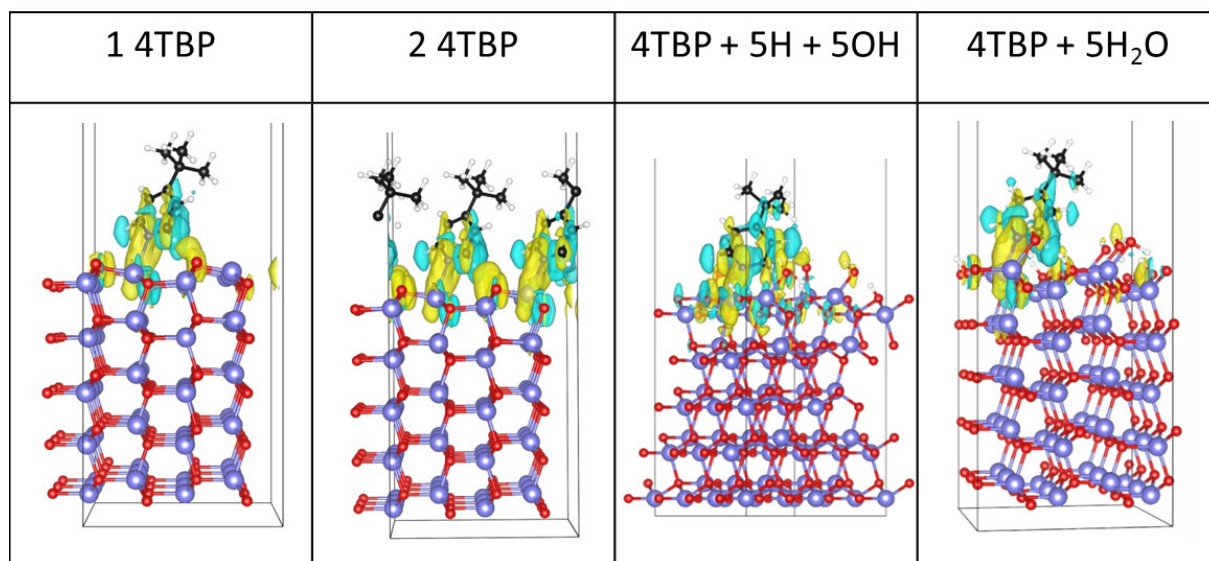
The charge density data files have been generated from the SIESTA output using the program DENCHAR available in the SIESTA package. All pictures have been generated with the VESTA software.

a) Benzoic acid on ZnO(10-10)



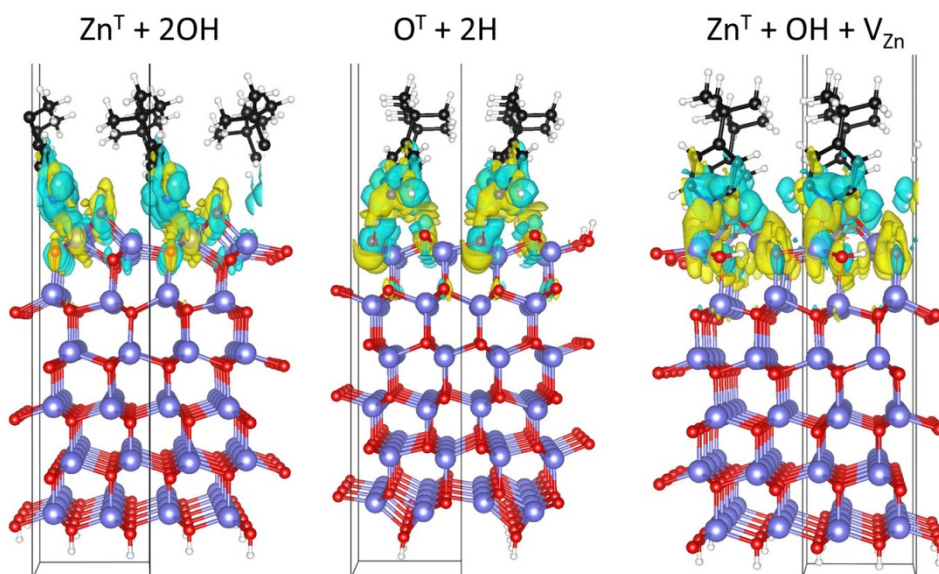
Charge density difference (isovalue  $0.005 \text{ e/\text{Å}^3}$ ) for BA-H adsorbed on ZnO(10-10). The three modes of anchoring are illustrated: (left) monodentate [BM1.2] ; (middle) bidentate [BM2.3] ; (right) chelate [BM3]

b) 4TBP (with and without co-adsorbant) on ZnO(10-10)



Charge density difference (isovalue  $0.005 \text{ e}/\text{\AA}^3$ ) for 4TBP on ZnO(10-10) in the different cases discussed in the paper (see text for the notation).

c) 4TBP on polar ZnO



Charge density difference (isovalue  $0.005 \text{ e}/\text{\AA}^3$ ) for 4TBP on polar ZnO using the models described in the text: Zn-terminated, O-terminated and Zn-terminated + vacancy. The unit cell is duplicated for sake of clarity.